

MOSFET - P-Channel Logic Level PowerTrench®

-40 V, 13.5 mΩ, -50 A

FDD9510L-F085

Features

- Typ $R_{DS(on)}$ = 11 mΩ at $V_{GS} = -10$ V; $I_D = -50$ A
- Typ $Q_{g(tot)}$ = 28 nC at $V_{GS} = -10$ V; $I_D = -50$ A
- UIS Capability
- Qualified to AEC Q101
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Electrical Power Steering
- Integrated Starter/Alternator
- Distributed Power Architectures and VRM
- Primary Switch for 12 V Systems

ABSOLUTE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain to Source Voltage	V_{DSS}	-40	V
Gate to Source Voltage	V_{GS}	± 16	V
Drain Current – Continuous ($V_{GS} = -10$ V) ($T_C = 25^\circ\text{C}$) (Note 1)	I_D	-50	A
Pulsed Drain Current ($T_C = 25^\circ\text{C}$)	I_D	See Figure 4	A
Single Pulse Avalanche Energy (Note 2)	E_{AS}	35.3	mJ
Power Dissipation	P_D	75	W
Derate above 25°C	P_D	0.5	W/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$
Thermal Resistance (Junction to Case)	$R_{\theta JC}$	2	$^\circ\text{C/W}$
Maximum Thermal Resistance (Junction to Ambient) (Note 3)	$R_{\theta JA}$	52	$^\circ\text{C/W}$

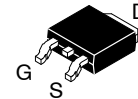
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Current is limited by wirebond configuration
2. Starting $T_J = 25^\circ\text{C}$, $L = 40$ μH , $I_{AS} = -42$ A, $V_{DD} = -40$ V during inductor charging and $V_{DD} = 0$ V during time in avalanche
3. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2 oz copper.

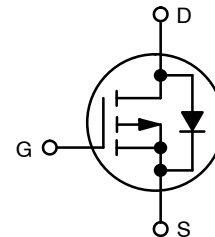


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**DPAK
TO-252
CASE 369AS**



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FDD9510L-F085

PACKAGE MARKING AND ORDERING INFORMATION

Device	Device Marking	Package	Reel Size	Tape Width	Quantity
FDD9510L-F085	FDD9510L	D-PAK (TO-252)	13"	16 mm	2500 Units

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} = 0 V, I _D = -250 μA		-40	-	-	V
I _{DSS}	Drain to Source Leakage Current	V _{DS} = -40 V, V _{GS} = 0 V	T _J = 25°C	-	-	-1	μA
			T _J = 175°C (Note 4)	-	-	-1	mA
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±16 V		-	-	±100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate to Source Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA		−1	−1.9	−3	V
R _{DS(on)}	Drain to Source On-Resistance	V _{GS} = −4.5 V, I _D = −50 A, T _J = 25°C		−	16	22	mΩ
		V _{GS} = −10 V, I _D = −50 A	T _J = 25°C	−	11	13.5	mΩ
			T _J = 175°C (Note 4)	−	18	22.7	mΩ

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = −20 V, V _{GS} = 0 V, f = 1 MHz		–	2020	–	pF
C _{oss}	Output Capacitance			–	785	–	pF
C _{rss}	Reverse Transfer Capacitance			–	36	–	pF
R _g	Gate Resistance	V _{GS} = −0.5 V, f = 1 MHz		–	23	–	Ω
Q _{g(tot)}	Total Gate Charge	V _{DD} = −20 V, I _D = −50 A	V _{GS} = 0 V to −10 V	–	28	37	nC
Q _{g(−4.5)}	Total Gate Charge		V _{GS} = 0 V to −4.5 V	–	13	–	nC
Q _{g(th)}	Threshold Gate Charge		V _{GS} = 0 V to −1 V	–	2	–	nC
Q _{gs}	Gate to Source Gate Charge	V _{DD} = −20 V, I _D = −50 A		–	7	–	nC
Q _{gd}	Gate to Drain “Miller” Charge			–	4	–	nC

SWITCHING CHARACTERISTICS

t_{on}	Turn-On Time	$V_{DD} = -20\text{ V}, I_D = -50\text{ A}, V_{GS} = -10\text{ V}, R_{GEN} = 6\text{ }\Omega$	-	-	44	ns
$t_{d(on)}$	Turn-On Delay Time		-	8	-	ns
t_r	Turn-On Rise Time		-	21	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	113	-	ns
t_f	Turn-Off Fall Time		-	35	-	ns
t_{off}	Turn-Off Time		-	-	220	ns

DRAIN-SOURCE DIODE CHARACTERISTICS

V_{SD}	Source to Drain Diode Voltage	$V_{GS} = 0\text{ V}, I_{SD} = -50\text{ A}$	-	-0.97	-1.25	V
		$V_{GS} = 0\text{ V}, I_{SD} = -25\text{ A}$	-	-0.9	-1.2	V
T_{rr}	Reverse Recovery Time	$I_F = -50\text{ A}, dI_{SD}/dt = 100\text{ A}/\mu\text{s}$	-	42	63	ns
Q_{rr}	Reverse Recovery Charge		-	31	56	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. The maximum value is specified by design at $T_J = 175^\circ\text{C}$. Product is not tested to this condition in production

TYPICAL CHARACTERISTICS

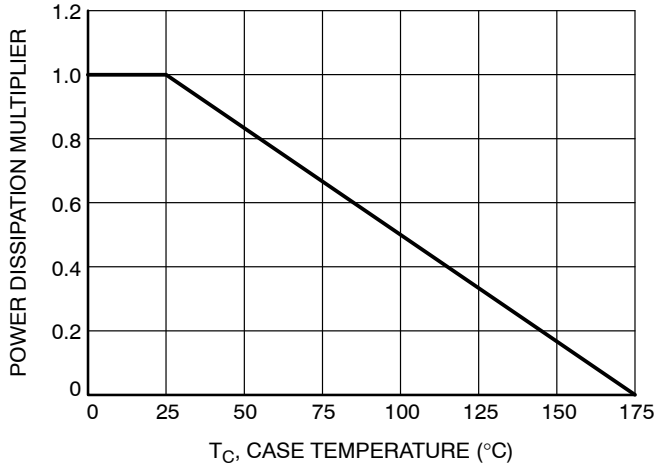


Figure 1. Normalized Power Dissipation vs. Case Temperature

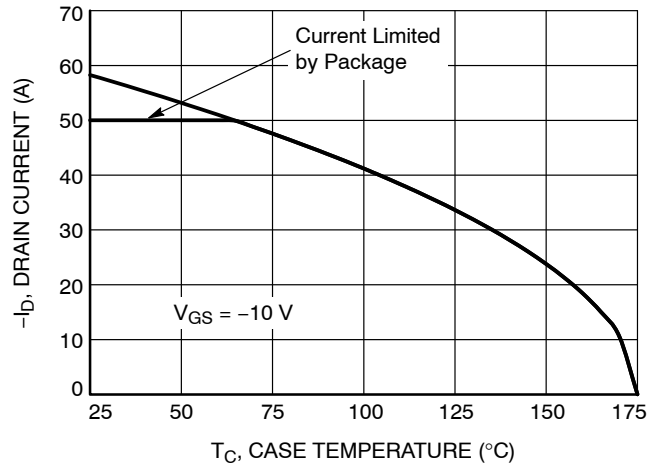


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

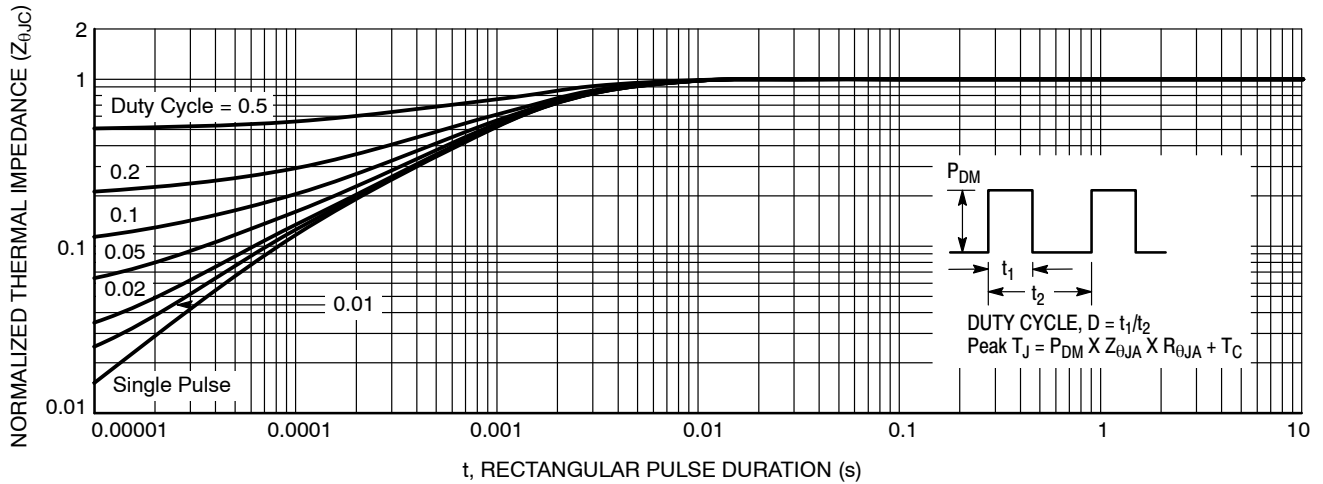


Figure 3. Normalized Maximum Transient Thermal Impedance

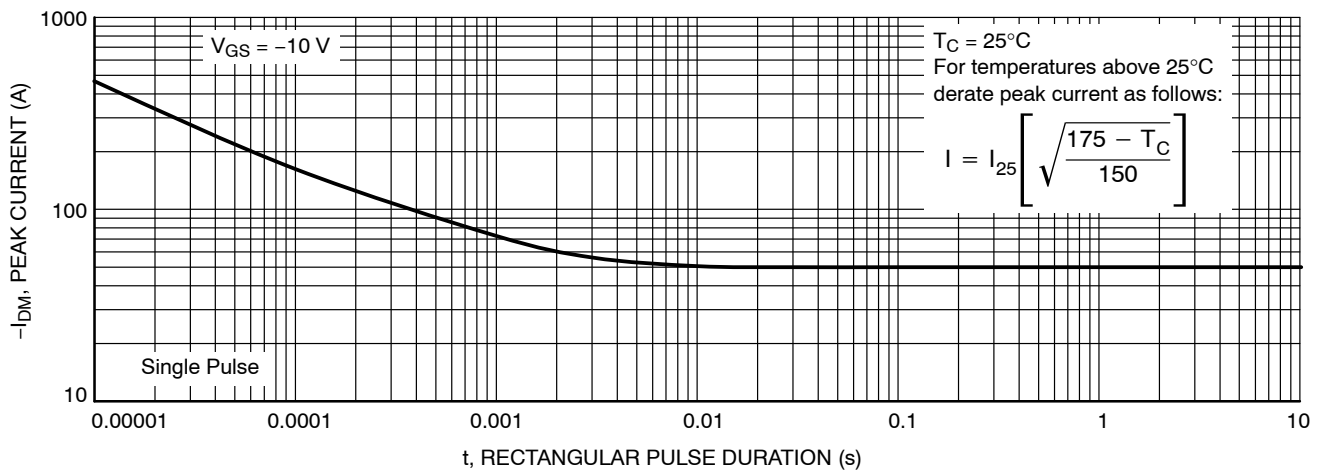


Figure 4. Peak Current Capability

TYPICAL CHARACTERISTICS

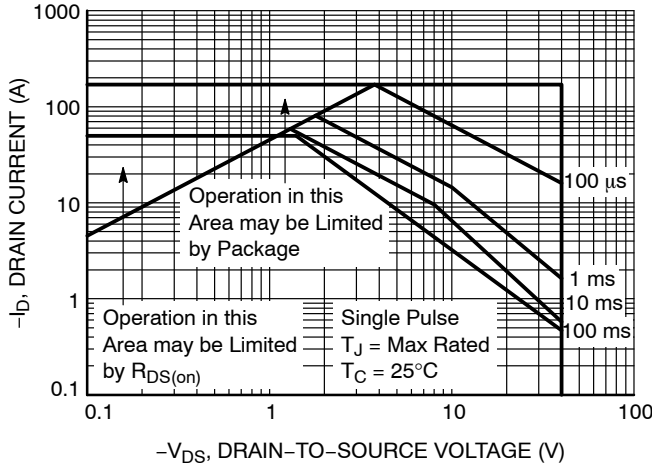


Figure 5. Forward Bias Safe Operating Area

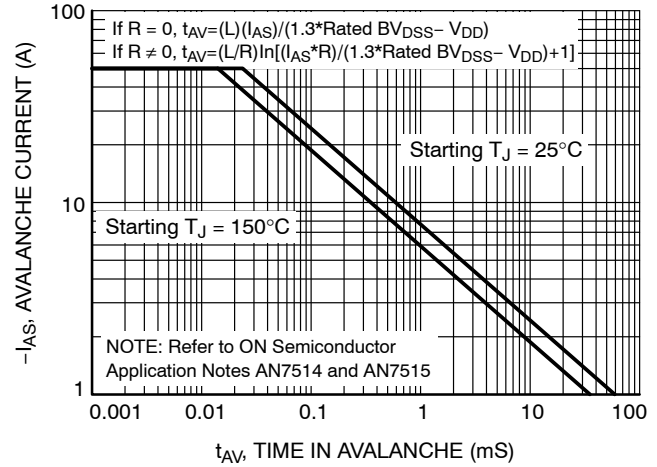


Figure 6. Unclamped Inductive Switching Capability

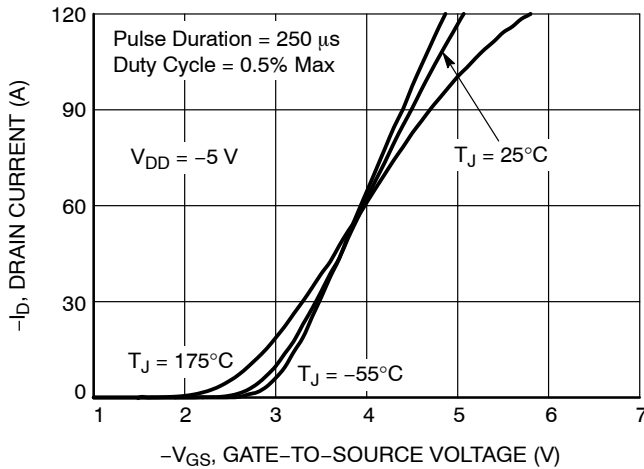


Figure 7. Transfer Characteristics

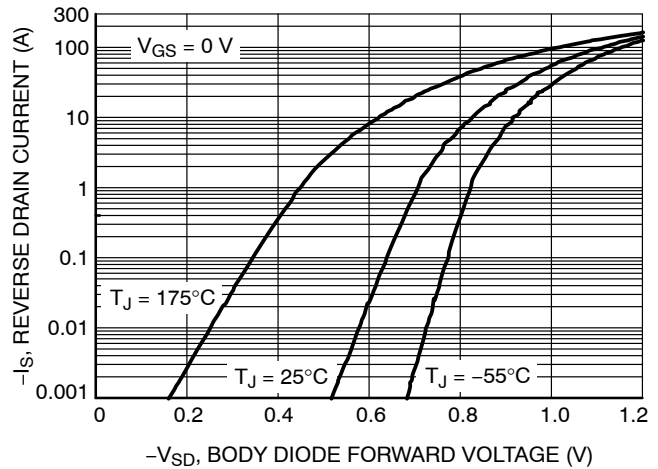


Figure 8. Forward Diode Characteristics

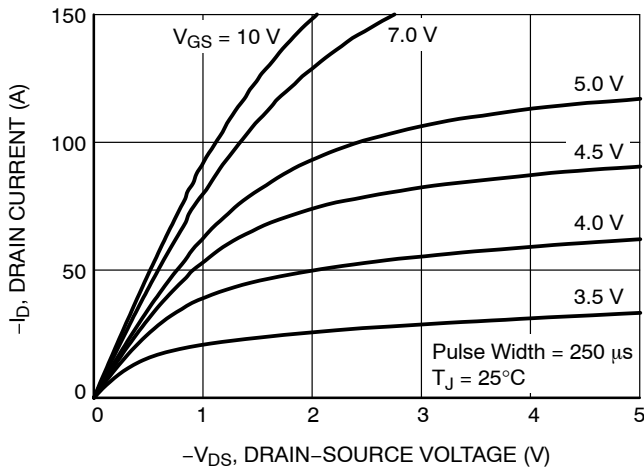


Figure 9. Saturation Characteristics

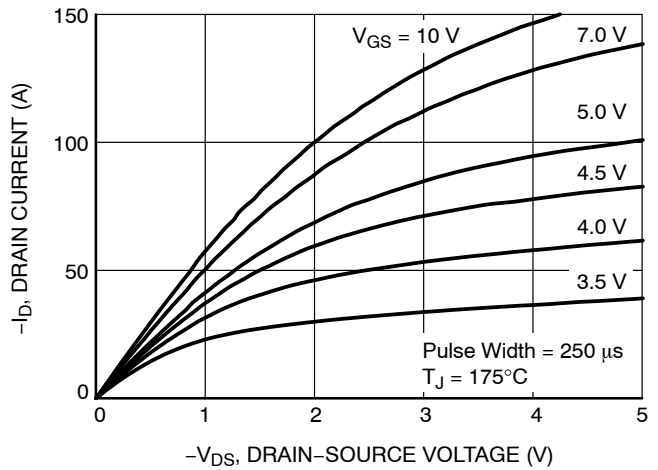


Figure 10. Saturation Characteristics

TYPICAL CHARACTERISTICS

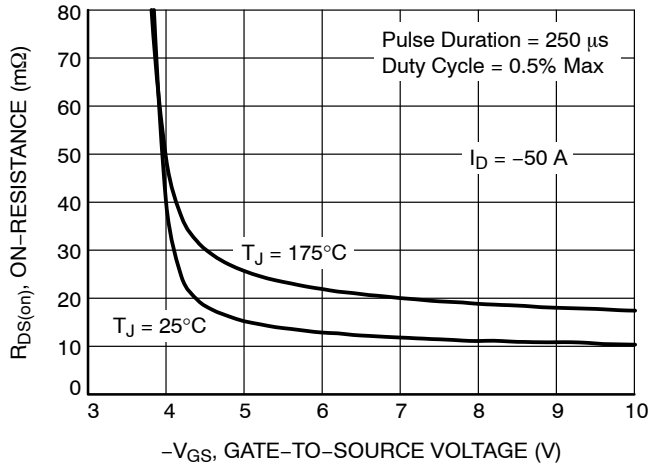
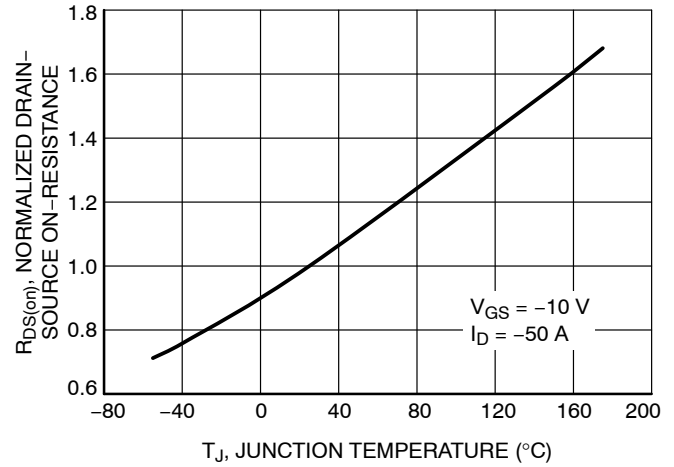
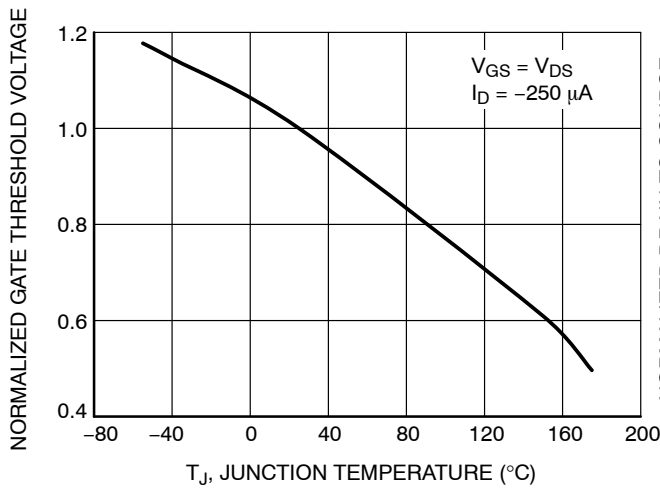
Figure 11. $R_{DS(on)}$ vs. Gate VoltageFigure 12. Normalized $R_{DS(on)}$ vs. Junction Temperature

Figure 13. Normalized Gate Threshold Voltage vs. Temperature

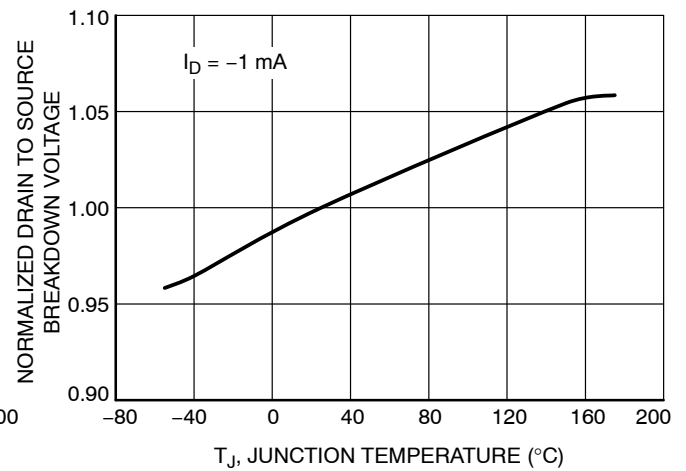


Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

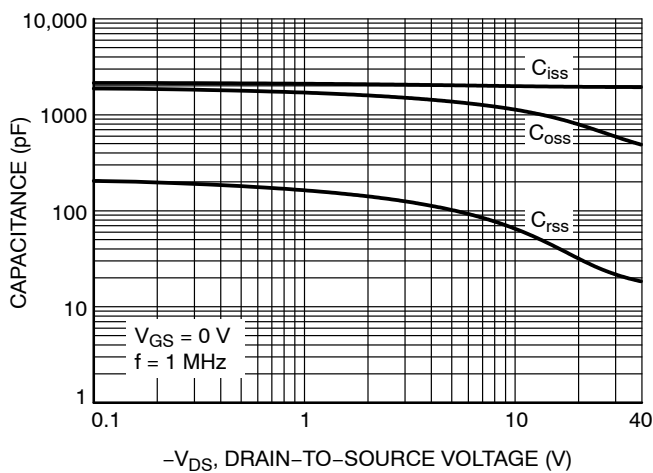


Figure 15. Capacitance vs. Drain to Source Voltage

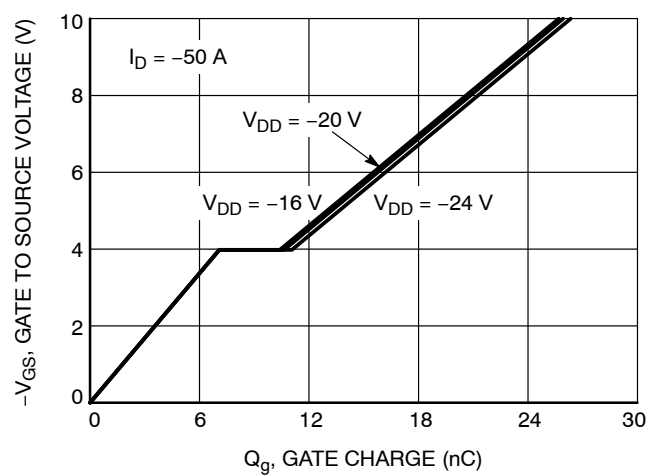
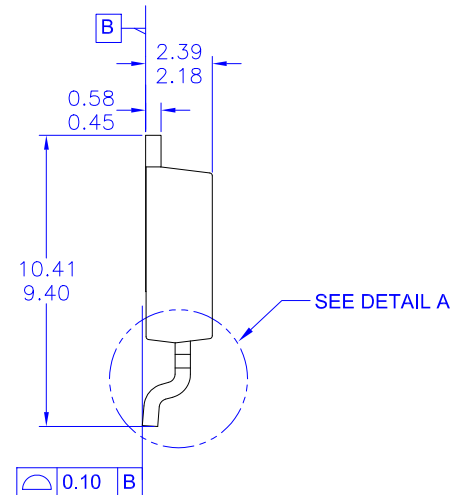
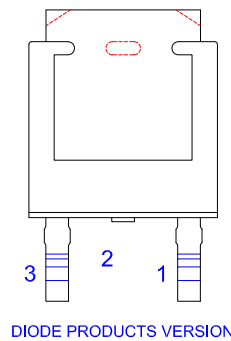
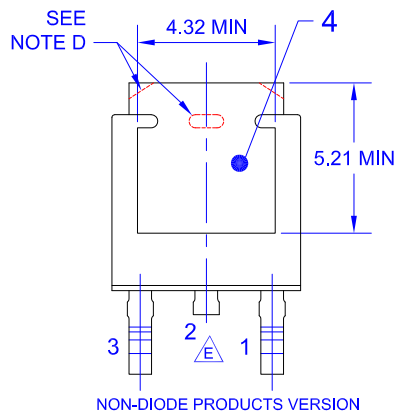
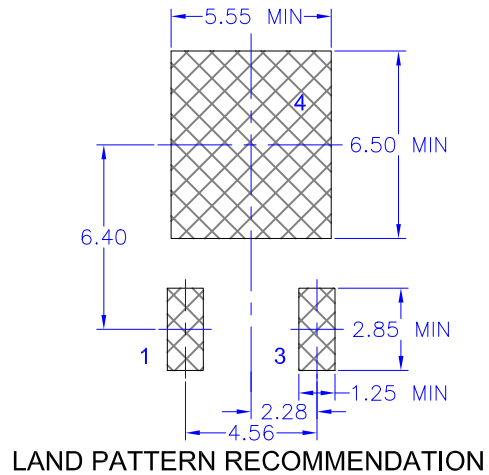
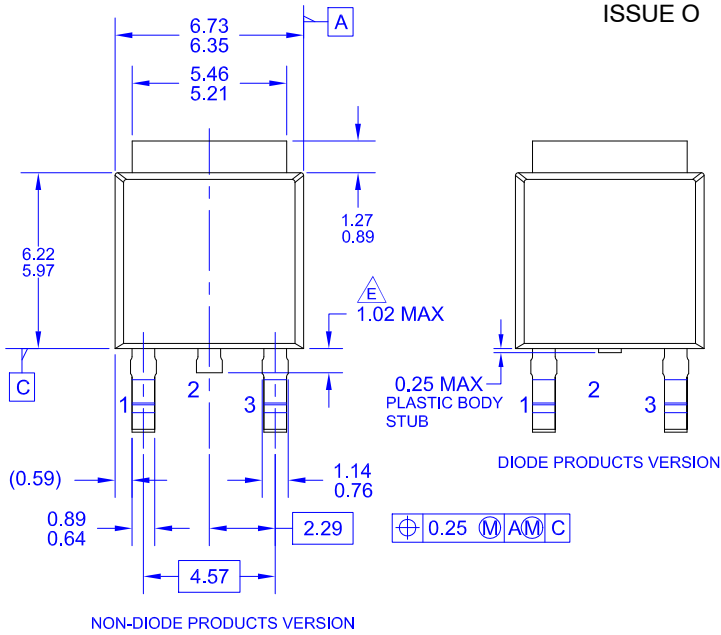


Figure 16. Gate Charge vs. Gate to Source Voltage

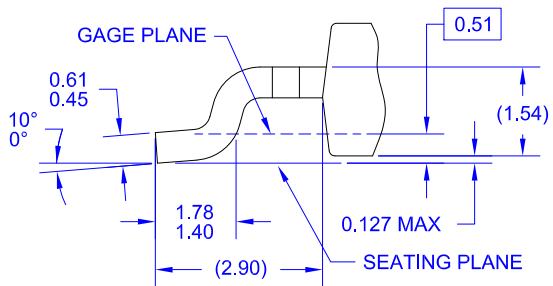
PACKAGE DIMENSIONS

DPAK3 (TO-252 3 LD)
CASE 369AS
ISSUE O



NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
- E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS
- F) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.



DETAIL A
(ROTATED -90°)
SCALE: 12X

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